Features

- Fast Read Access Time 120 ns
- Fast Byte Write 200 µs or 1 ms
- Self-timed Byte Write Cycle
 - Internal Address and Data Latches
 - Internal Control Timer
 - Automatic Clear Before Write
- Direct Microprocessor Control
 - READY/BUSY Open Drain Output
 - DATA Polling
- Low Power
 - 30 mA Active Current
 - 100 µA CMOS Standby Current
- High Reliability
 - Endurance: 10⁴ or 10⁵ Cycles
 - Data Retention: 10 Years
- 5V ± 10% Supply
- CMOS and TTL Compatible Inputs and Outputs
- JEDEC Approved Byte-wide Pinout
- Commercial and Industrial Temperature Ranges

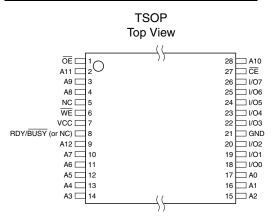
Description

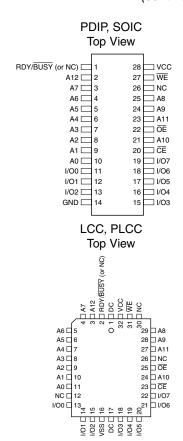
The AT28C64 is a low-power, high-performance 8,192 words by 8-bit nonvolatile electrically erasable and programmable read only memory with popular, easy-to-use features. The device is manufactured with Atmel's reliable nonvolatile technology.

(continued)

Pin Configurations

Pin Name	Function
A0 - A12	Addresses
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
RDY/BUSY	Ready/Busy Output
NC	No Connect
DC	Don't Connect





Note: PLCC package pins 1 and 17 are DON'T CONNECT.





64K (8K x 8)
Parallel
EEPROMs

AT28C64 AT28C64X

Rev. 0001H-12/99



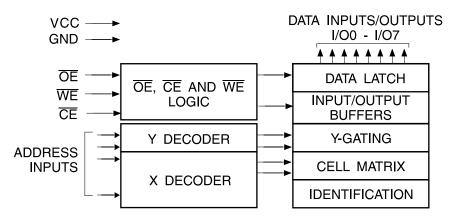
The AT28C64 is accessed like a Static RAM for the read or write cycles without the need for external components. During a byte write, the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of a write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. The device includes two methods for detecting the end of a write cycle, level detection of RDY/BUSY (unless pin 1 is N.C.) and DATA Polling of I/O₇. Once the end of a write

cycle has been detected, a new access for a read or write can begin.

The CMOS technology offers fast access times of 120 ns at low power dissipation. When the chip is deselected the standby current is less than 100 μ A.

Atmel's AT28C64 has additional features to ensure high quality and manufacturability. The device utilizes error correction internally for extended endurance and for improved data retention characteristics. An extra 32 bytes of EEPROM are available for device identification or tracking.

Block Diagram



Absolute Maximum Ratings*

	_
Temperature under Bias .	55°C to +125°C
Storage Temperature	65°C to +150°C
All Input Voltages (includi with Respect to Ground	ng NC Pins) 0.6V to +6.25V
All Output Voltages with Respect to Ground	0.6V to V _{CC} + 0.6V
Voltage on OE and A9 with Respect to Ground	0.6V to +13.5V

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

Device Operation

READ: The AT28C64 is accessed like a Static RAM. When \overline{CE} and \overline{OE} are low and \overline{WE} is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in a high impedance state whenever \overline{CE} or \overline{OE} is high. This dual line control gives designers increased flexibility in preventing bus contention.

BYTE WRITE: Writing data into the AT28C64 is similar to writing into a Static RAM. A low pulse on the \overline{WE} or \overline{CE} input with \overline{OE} high and \overline{CE} or \overline{WE} low (respectively) initiates a byte write. The address location is latched on the falling edge of \overline{WE} (or \overline{CE}); the new data is latched on the rising edge. Internally, the device performs a self-clear before write. Once a byte write has been started, it will automatically time itself to completion. Once a programming operation has been initiated and for the duration of t_{WC} , a read operation will effectively be a polling operation.

FAST BYTE WRITE: The AT28C64E offers a byte write time of 200 µs maximum. This feature allows the entire device to be rewritten in 1.6 seconds.

READY/BUSY: Pin 1 is an open drain RDY/BUSY output that can be used to detect the end of a write cycle. RDY/BUSY is actively pulled low during the write cycle and is released at the completion of the write. The open drain connection allows for OR-tying of several devices to the

same RDY/BUSY line. The RDY/BUSY pin is not connected for the AT28C64X.

DATA POLLING: The AT28C64 provides DATA Polling to signal the completion of a write cycle. During a write cycle, an attempted read of the data being written results in the complement of that data for I/O₇ (the other outputs are indeterminate). When the write cycle is finished, true data appears on all outputs.

WRITE PROTECTION: Inadvertent writes to the device are protected against in the following ways: (a) V_{CC} sense – if V_{CC} is below 3.8V (typical) the write function is inhibited; (b) V_{CC} power on delay – once V_{CC} has reached 3.8V the device will automatically time out 5 ms (typical) before allowing a byte write; and (c) write inhibit – holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits byte write cycles.

CHIP CLEAR: The contents of the entire memory of the AT28C64 may be set to the high state by the CHIP CLEAR operation. By setting \overline{CE} low and \overline{OE} to 12 volts, the chip is cleared when a 10 msec low pulse is applied to \overline{WE} .

DEVICE IDENTIFICATION: An extra 32 bytes of EEPROM memory are available to the user for device identification. By raising A9 to $12\pm0.5V$ and using address locations 1FE0H to 1FFFH the additional bytes may be written to or read from in the same manner as the regular memory array.





DC and AC Operating Range

		AT28C64-12	AT28C64-15	AT28C64-20	AT28C64-25
Operating	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C
Temperature (Case)	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
V _{CC} Power Supply	•	5V ± 10%	5V ± 10%	5V ± 10%	5V ± 10%

Operating Modes

Mode	CE	ŌE	WE	I/O
Read	V _{IL}	V _{IL}	V _{IH}	D _{OUT}
Write ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	D _{IN}
Standby/Write Inhibit	V _{IH}	X ⁽¹⁾	Х	High Z
Write Inhibit	Х	Х	V _{IH}	
Write Inhibit	Х	V _{IL}	Х	
Output Disable	Х	V _{IH}	Х	High Z
Chip Erase	V _{IL}	V _H ⁽³⁾	V _{IL}	High Z

Notes: 1. X can be V_{IL} or V_{IH}.

2. Refer to AC programming waveforms.

3. $V_H = 12.0V \pm 0.5V$.

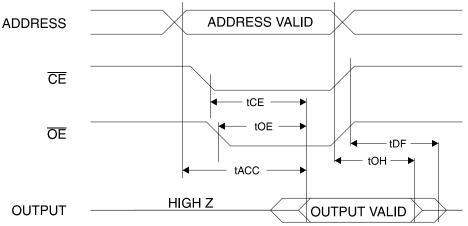
DC Characteristics

Symbol	Parameter	Condition	Min	Max	Units	
I _{LI}	Input Load Current	$V_{IN} = 0V \text{ to } V_{CC} + 1V$			10	μΑ
I _{LO}	Output Leakage Current	$V_{I/O} = 0V \text{ to } V_{CC}$			10	μΑ
I _{SB1}	V _{CC} Standby Current CMOS	$\overline{\text{CE}} = \text{V}_{\text{CC}} - 0.3 \text{V to V}_{\text{CC}} + 1.0$	V		100	μA
	V Standby Current TTI	<u>CE</u> 2.0V+c.V . 1.0V	Com.		2	mA
I _{SB2}	V _{CC} Standby Current TTL	$\overline{\text{CE}} = 2.0 \text{V to V}_{\text{CC}} + 1.0 \text{V}$	Ind.		3	mA
	V Active Current AC	f = 5 MHz; I _{OUT} = 0 mA	Com.		30	mA
I _{CC}	V _{CC} Active Current AC	CE = V _{IL}	Ind.		45	mA
V _{IL}	Input Low Voltage		•		0.8	V
V _{IH}	Input High Voltage			2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA = 4.0 mA for RDY/ BUSY			0.45	V
V _{OH}	Output High Voltage	I _{OH} = -400 μA		2.4		V

AC Read Characteristics

		AT28C64-12		AT28C64-15 AT28C		C64-20 AT28		C64-25		
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max	Units
t _{ACC}	Address to Output Delay		120		150		200		250	ns
t _{CE} ⁽¹⁾	CE to Output Delay		120		150		200		250	ns
t _{OE} ⁽²⁾	OE to Output Delay	10	60	10	70	10	80	10	100	ns
t _{DF} ⁽³⁾⁽⁴⁾	CE or OE High to Output Float	0	45	0	50	0	55	0	60	ns
t _{OH}	Output Hold from \overline{OE} , \overline{CE} or Address, whichever occurred first	0		0		0		0		ns

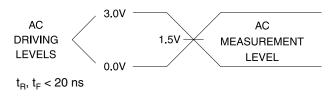
AC Read Waveforms⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾



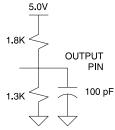
Notes: 1. $\overline{\text{CE}}$ may be delayed up to t_{ACC} - t_{CE} after the address transition without impact on t_{ACC} .

- 2. $\overline{\text{OE}}$ may be delayed up to t_{CE} t_{OE} after the falling edge of $\overline{\text{CE}}$ without impact on t_{CE} or by t_{ACC} t_{OE} after an address change without impact on t_{ACC} .
- 3. t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first ($C_L = 5 \text{ pF}$).
- 4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



Output Test Load



Pin Capacitance

 $f = 1 \text{ MHz}, T = 25^{\circ}C^{(1)}$

Symbol	Тур	Max	Units	Conditions
C _{IN}	4	6	pF	$V_{IN} = 0V$
C _{OUT}	8	12	pF	V _{OUT} = 0V

Note: 1. This parameter is characterized and is not 100% tested.



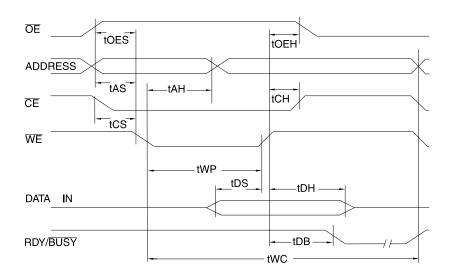


AC Write Characteristics

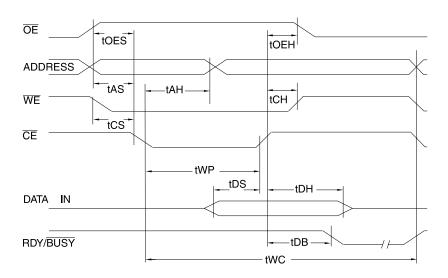
Symbol	Parameter		Min	Max	Units
t _{AS} , t _{OES}	Address, OE Setup Time		10		ns
t _{AH}	Address Hold Time		50		ns
t _{WP}	Write Pulse Width (WE or CE)		100	1000	ns
t _{DS}	Data Setup Time	50		ns	
t _{DH} , t _{OEH}	Data, OE Hold Time		10		ns
t _{CS} , t _{CH}	CE to WE and WE to CE Setup and Ho	ld Time	0		ns
t _{DB}	Time to Device Busy		50	ns	
	Write Cycle Time (ention evailable)	AT28C64		1	ms
t _{WC}	Write Cycle Time (option available)		200	μs	

AC Write Waveforms

WE Controlled



CE Controlled



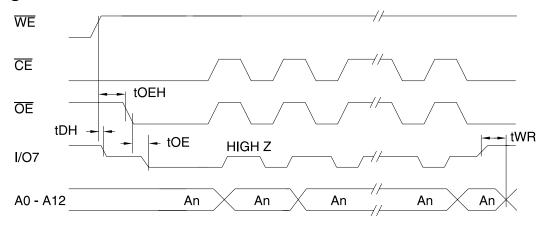
Data Polling Characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	10			ns
t _{OEH}	OE Hold Time	10			ns
t _{OE}	OE to Output Delay ⁽²⁾				ns
t _{WR}	Write Recovery Time	0			ns

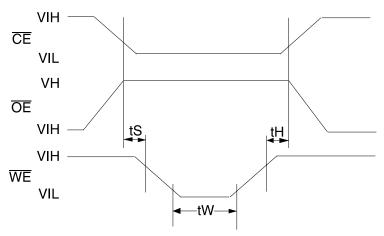
Notes: 1. These parameters are characterized and not 100% tested.

2. See "AC Read Characteristics".

Data Polling Waveforms



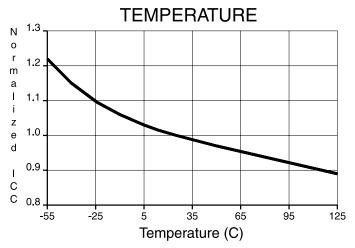
Chip Erase Waveforms



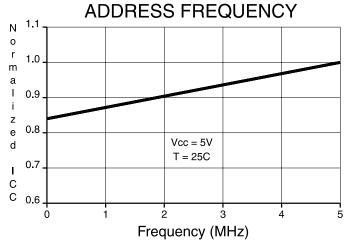
$$\begin{split} t_S &= t_H = 1 \text{ } \mu\text{sec (min.)} \\ t_W &= 10 \text{ } m\text{sec (min.)} \\ V_H &= 12.0 \pm 0.5 V \end{split}$$



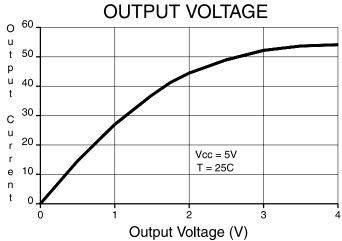
NORMALIZED SUPPLY CURRENT vs.



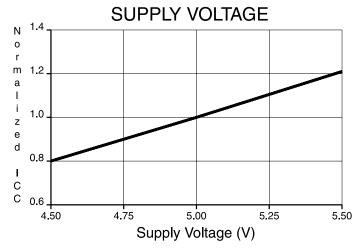
NORMALIZED SUPPLY CURRENT vs.



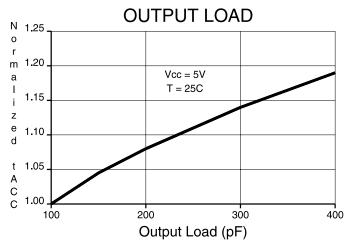
OUTPUT SINK CURRENT vs.



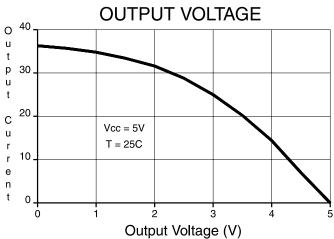
NORMALIZED SUPPLY CURRENT vs.



NORMALIZED ACCESS TIME vs.



OUTPUT SOURCE CURRENT vs.



AT28C64 Ordering Information

t _{ACC}	I _{cc}	(mA)			
(ns)	Active	Standby	Ordering Code	Package	Operation Range
120	30	0.1	AT28C64-12JC	32J	Commercial
			AT28C64-12PC	28P6	(0°C to 70°C)
			AT28C64-12SC	28S	
			AT28C64-12TC	28T	
	45	0.1	AT28C64-12JI	32J	Industrial
			AT28C64-12PI	28P6	(-40°C to 85°C)
			AT28C64-12SI	28S	
			AT28C64-12TI	28T	
150	30	0.1	AT28C64-15JC	32J	Commercial
			AT28C64-15PC	28P6	(0°C to 70°C)
			AT28C64-15SC	28S	
			AT28C64-15TC	28T	
	45	0.1	AT28C64-15JI	32J	Industrial
			AT28C64-15PI	28P6	(-40°C to 85°C)
			AT28C64-15SI	28S	
			AT28C64-15TI	28T	
200	30	0.1	AT28C64-20JC	32J	Commercial
			AT28C64-20PC	28P6	(0°C to 70°C)
			AT28C64-20SC	28S	
			AT28C64-20TC	28T	
	45	0.1	AT28C64-20JI	32J	Industrial
			AT28C64-20PI	28P6	(-40°C to 85°C)
			AT28C64-20SI	28S	
			AT28C64-20TI	28T	
250	30	0.1	AT28C64-25JC	32J	Commercial
			AT28C64-25PC	28P6	(0°C to 70°C)
			AT28C64-25SC	28S	
			AT28C64-25TC	28T	
	45	0.1	AT28C64-25JI	32J	Industrial
			AT28C64-25PI	28P6	(-40°C to 85°C)
			AT28C64-25SI	28S	
			AT28C64-25TI	28T	

	Package Type					
32J	J 32-lead, Plastic J-leaded Chip Carrier (PLCC)					
28P6	P6 28-lead, 0.600" Wide, Plastic Dull Inline Package (PDIP)					
28S	28-lead, 0.300" Wide, Plastic Gull Wing, Small Outline (SOIC)					
28T	28-lead, Plastic Thin Small Outline Package (TSOP)					
	Options					
Blank	Blank Standard Device: Endurance = 10K Write Cycles; Write Time = 1 ms					
E	High Endurance Option: Endurance = 100K Write Cycles; Write Time = 200 μs					





AT28C64X Ordering Information

t _{ACC}	I _{cc}	(mA)			
(ns)	Active	Standby	Ordering Code	Package	Operation Range
150	30	0.1	AT28C64X-15JC	32J	Commercial
			AT28C64X-15PC	28P6	(0°C to 70°C)
			AT28C64X-15SC	28S	
			AT28C64X-15TC	28T	
	45	0.1	AT28C64X-15JI	32J	Industrial
			AT28C64X-15PI	28P6	(-40°C to 85°C)
			AT28C64X-15SI	28S	
			AT28C64X-15TI	28T	
200	30	0.1	AT28C64X-20JC	32J	Commercial
			AT28C64X-20PC	28P6	(0°C to 70°C)
			AT28C64X-20SC	28S	
			AT28C64X-20TC	28T	
	45	0.1	AT28C64X-20JI	32J	Industrial
			AT28C64X-20PI	28P6	(-40°C to 85°C)
			AT28C64X-20SI	28S	
			AT28C64X-20TI	28T	
250	30	0.1	AT28C64X-25JC	32J	Commercial
			AT28C64X-25PC	28P6	(0°C to 70°C)
			AT28C64X-25SC	28S	
			AT28C64X-25TC	28T	
	45	0.1	AT28C64X-25JI	32J	Industrial
			AT28C64X-25PI	28P6	(-40°C to 85°C)
			AT28C64X-25SI	28S	
			AT28C64X-25TI	28T	

Valid Part Numbers

The following table lists standard Atmel products that can be ordered.

Device Numbers	Speed	Package and Temperature Combinations
AT28C64 X	12	JC, JI, PC, PI, SC, SI, TC, TI
AT28C64 X	15	JC, JI, PC, PI, SC, SI, TC, TI
AT28C64 X	20	JC, JI, PC, PI, SC, SI, TC, TI
AT28C64 X	25	JC, JI, PC, PI, SC, SI, TC, TI

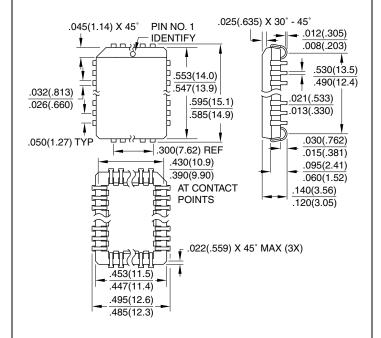
Die Products

Reference Section: Parallel EEPROM Die Products

Package Type		
32J	32-lead, Plastic J-leaded Chip Carrier (PLCC)	
28P6	28-lead, 0.600" Wide, Plastic Dull Inline Package (PDIP)	
28\$	28-lead, 0.300" Wide, Plastic Gull Wing, Small Outline (SOIC)	
28T	28-lead, Plastic Thin Small Outline Package (TSOP)	

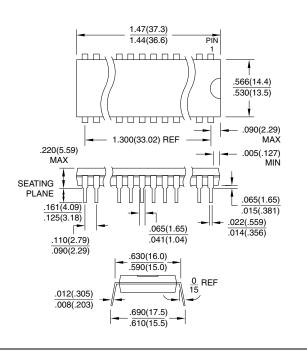
Packaging Information

32J, 32-lead, Plastic J-leaded Chip Carrier (PLCC) Dimensions in Inches and (Millimeters) JEDEC STANDARD MS-016 AE



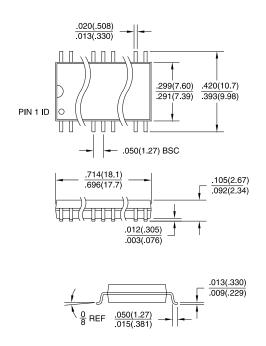
28P6, 28-lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)

Dimensions in Inches and (Millimeters) JEDEC STANDARD MS-011 AB



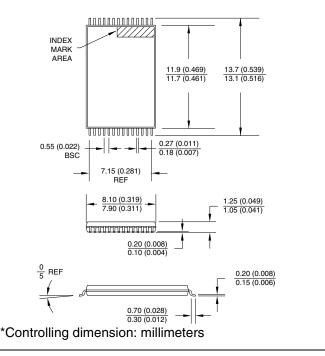
28S, 28-lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)

Dimensions in Inches and (Millimeters)



28T, 28-lead, Plastic Thin Small Outline Package (TSOP)

Dimensions in Millimeters and (Inches)*







Atmel Headquarters

Corporate Headquarters 2325 Orchard Parkway San Jose, CA 95131 TEL (408) 441-0311 FAX (408) 487-2600

Europe

Atmel U.K., Ltd.
Coliseum Business Centre
Riverside Way
Camberley, Surrey GU15 3YL
England
TEL (44) 1276-686-677
FAX (44) 1276-686-697

Asia

Atmel Asia, Ltd. Room 1219 Chinachem Golden Plaza 77 Mody Road Tsimhatsui East Kowloon Hong Kong TEL (852) 2721-9778 FAX (852) 2722-1369

Japan

Atmel Japan K.K. 9F, Tonetsu Shinkawa Bldg. 1-24-8 Shinkawa Chuo-ku, Tokyo 104-0033 Japan TEL (81) 3-3523-3551 FAX (81) 3-3523-7581

Atmel Operations

Atmel Colorado Springs 1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906 TEL (719) 576-3300 FAX (719) 540-1759

Atmel Rousset
Zone Industrielle
13106 Rousset Cedex
France
TEL (33) 4-4253-6000
FAX (33) 4-4253-6001

Fax-on-Demand North America: 1-(800) 292-8635 International: 1-(408) 441-0732

e-mail literature@atmel.com

Web Site http://www.atmel.com

BBS 1-(408) 436-4309

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